2012 EDS Paul Rappaport Award

Kelin J. Kuhn

A high priority of the Electron Devices Society is to recognize and enhance the quality of papers published in EDS archival literature. Every year, the Society confers its prestigious Paul Rappaport Award to the best paper published in the IEEE Transactions on Electron Devices. Among other criteria including technical excellence, an important metric for selection for the award is comprehensive and impartial referencing of prior art. The winning paper was selected from close to 550 articles that were published in 2012. The winning paper is entitled, "Considerations for Ultimate CMOS Scaling." This paper was published in the July, 2012 issue of the *IEEE Transactions on Electron Devices,* and was authored by Kelin J. Kuhn. The award will be presented at the EDS Board of Governors Meeting to be held in early December 2013, in Washington, D.C. In addition to the award certificate, the author will receive a check for $2,500. On behalf of the Electron Devices Society, I would like to congratulate Kelin Kuhn for this achievement. A brief biography of the author is given below.

Dr. Kelin J. Kuhn is an Intel Fellow and Director of Advanced Device Technology in the Technology and Manufacturing Group of the Intel Corporation. Dr. Kuhn joined Intel in 1997 and has been involved in Intel's technology development for the 0.35 micron, 130 nm, 90 nm, 45 nm, 22 nm and 14 nm technology nodes. Previously, she was an Associate Professor in the Department of Electrical and Computer Engineering at the University of Washington. Dr. Kuhn is an IEEE Fellow, the past recipient of a National Science Foundation Presidential Young Investigator Award for her work on strained layer III-V materials and two Intel IAA awards, one for her work on Hi-K metal gate transistors and one for her work on the 22 nm TriGate transistor. Dr. Kuhn earned her bachelor's degree in electrical engineering from the University of Washington in 1980. She received her master's and doctoral degrees in electrical engineering from Stanford University in 1985.

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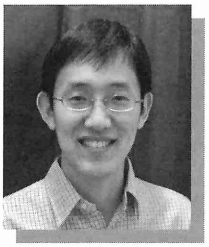
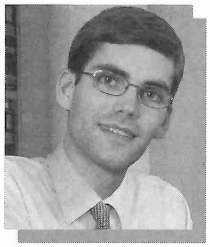
2012 George E. Smith Award

A high priority of the Electron Devices Society (EDS) is to recognize and enhance the quality of papers published in EDS archival literature. The George E. Smith Award was established in 2002 to recognize the best paper appearing in a fast turnaround archival publication of EDS, targeted to *IEEE Electron Device Letters*. Among other criteria including technical excellence, an important metric for selection for the award is comprehensive and impartial referencing of prior art.

The paper winning the 2012 George E. Smith Award was selected from among 500 articles that were published in 2012. The article is entitled *"Tri-Gate Normally-Off GaN Power MISFET."* This paper appeared in the March, 2012 issue of *IEEE Electron Device Letters,* and was authored by Bin Lu, Elison Matioli and Tomás Palacios. The award will be presented at the IEEE International Electron Devices Meeting (IEDM) to be held in early December, 2013 in Washington, D.C. In addition to the award certificate, the authors will receive a check for $2,500. On behalf of the Electron Devices Society I would like to congratulate the authors for this achievement. Brief biographies of the authors follow.



Bin Lu received his B.S. degree from Tsinghua University, Beijing, China, in 2006 and the M.S. and Ph.D. degrees from the Massachusetts Institute of Technology in 2007 and 2013, respectively, all in Electrical Engineering. His current research interest is on GaN-based power semiconductor devices.



Tomas Palacios is the Emmanuel Landsman CD Associate Professor in the Department of Electrical Engineering and Computer Science at the Massachusetts Institute of Technology, where he leads the Advanced Semiconductor Materials and Devices Group. His research focuses on the combination of new semiconductor materials and device concepts to advance the fields of information technology, biosensors and energy conversion. His work has been recognized with multiple awards including the 2011 Presidential Early Career Award for Scientists and Engineers (PECASE) and numerous best paper awards. Prof. Palacios has authored more than 200 contributions on advanced semiconductor devices in international journals and conferences,